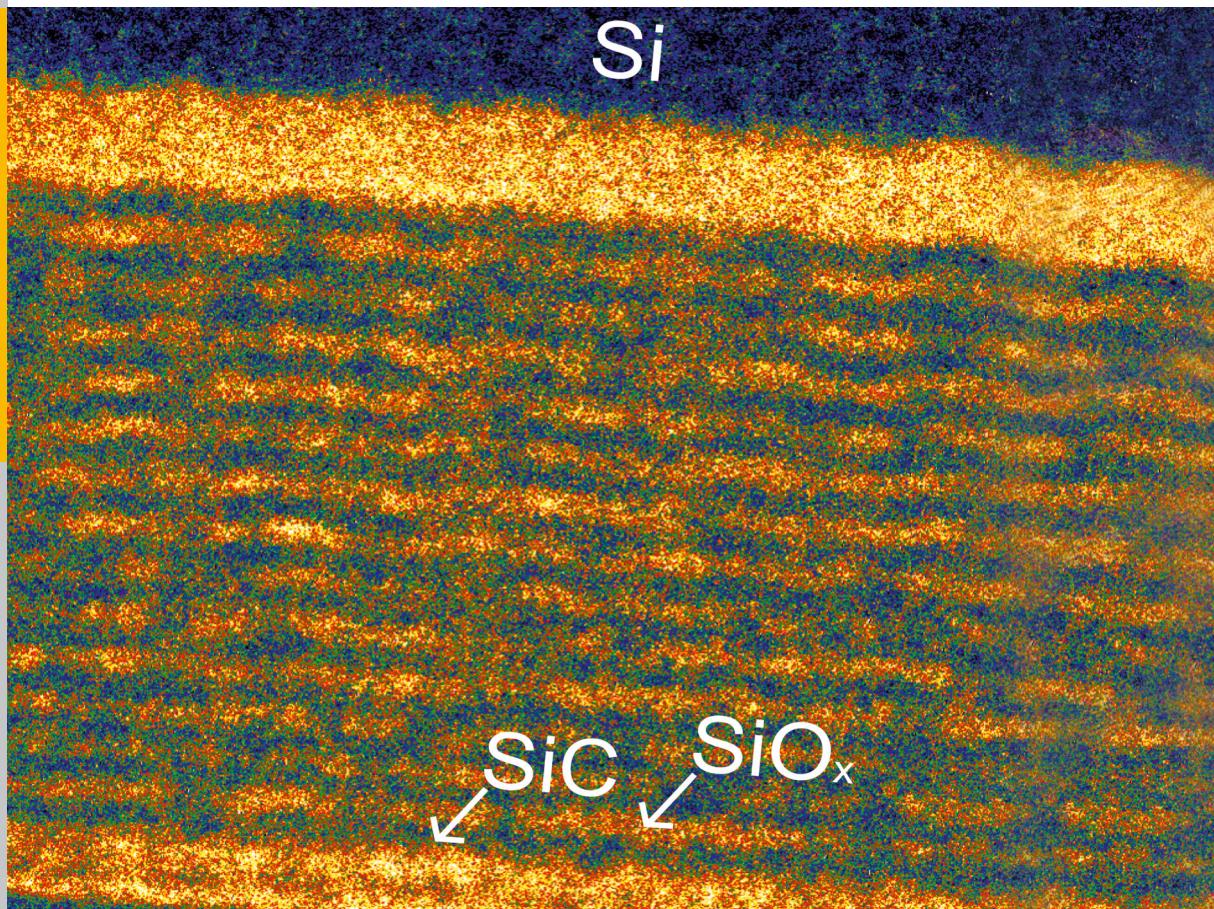


# Nanostructured Si-alloys for silicon solar cells

Kaining Ding



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